



DEC. 22 2003

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1

of 1

Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Complete If Known

Application Number	10/649,712
Filing Date	August 26, 2003
First Named Inventor	Ren, Fan
Art Unit	2812
Examiner Name	
Attorney Docket Number	5853-274

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

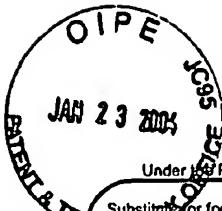
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>JMB</i>		Hu et al., "Enhancement mode AlGaN/GaN HFET with selectively grown pn junction gate," Electronics Letters, 36: 753-754, 2000.	
		Chen et al., "GaN Metal-insulator-semiconductor Field Effect Transistor Based on GaN/AlGaN Double Hetrojunctions," Nanjing University, P.R. China.	
		Yoshida, S. , Abstrat, "AlGaN/GaN Power FET," Furukawa Review, 21: 7-11, 2002.	
		Valizadeh, P., Abstrat, "Al _x Ga _{1-x} N/GaN High Electron Mobility Transistor (HEMT).	

Examiner Signature	<i>JMB</i>	Date Considered	<i>9/25/04</i>
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PTO/SB/08B (08-03)

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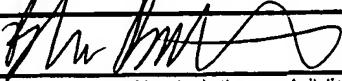
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
BWB		Kim et al., "Inversion behavior in Sc ₂ O ₃ /GaN gated diodes," Appl. Phys. Lett., 81: 373-375, July 2002.	
		Simin et al., "7.5kW/mm ² current switch using AlGaN/GaN metal-oxide-semiconductor heterostructure field effect transistor on SiC substrates," Electronics Letters, 36: November 2000.	
		Mistele et al., "First AlGaN/GaN MOSFET with photoanodic gate dielectric," Materials Science and Engineering, B93, 107-111, 2002.	
		Khan et al., "Enhancement and depletion mode GaN/AlGaN heterostructure field effect transistors," Appl. Phys. Lett., 68: 514-516, January 1996.	
		Simin, et al., "SiO ₂ /AlGaN/InGaN/GaN MOSDHFETs," IEEE Electron Device Letters, 23: 458-460, August 2002.	
		Kim et al., "Characteristics of MgO/GaN gate-controlled metal-oxide-semiconductor diodes," Applied Physics Letter, 80: 4555-4557, June 2002.	
		Koudymov et al., "Maximum current in nitride-based heterostructure field-effect transistors," Applied Physics Letters, 80: 3216-3218, April 2002.	
		Hu et al., "Si ₃ N ₄ /AlGaN/GaN-metal-insulator-semiconductor heterostructure field-effect transistors," Applied Physics Letters, 79: 2832-2834, October 2001.	
		Teles et al., "Spinodal decomposition in B _x Ga _{1-x} N and B _x Al _{1-x} N alloys," Applied Physics Letters, 80: 1177-1179, February 2002.	
✓		Chou et al., AlGaN/GaN Metal Oxide Semiconductor Heterostructure Field-Effect Transistor Based on a Liquid Phase Deposited Oxide," Jpn. J. Appl. Phys. 41: L748-L750, July 2002.	

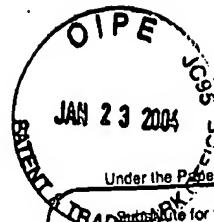
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Part 1 of 4 for form 1449/PTO

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PTO/SB/08A (08-03)

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Signature** *9/25/04* **Considered** *10/10/04*
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